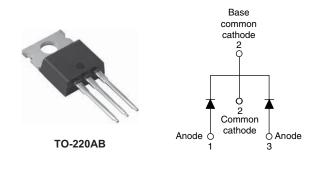
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VS-MUR1620CTPbF, VS-MUR1620CT-N3

Vishay Semiconductors

Ultrafast Rectifier, 2 x 8 A FRED Pt[®]



PRODUCT SUMMARY						
Package	TO-220AB					
I _{F(AV)}	2 x 8 A					
V _R	200 V					
V _F at I _F	0.895 V					
t _{rr} typ.	See Recovery table					
T _J max.	175 °C					
Diode variation	Common cathode					

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- · Designed and gualified according to JEDĔC[®]-JESD 47



COMPLIANT

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

VS-MUR1620CTPbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time guarantee the best overall performance, control, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage		V _{RRM}		200	V			
	per leg	I _{F(AV)}		8.0				
Average rectified forward current	total device		Rated V_R , T_C = 150 °C	16	А			
Non-repetitive peak surge current per leg		I _{FSM}		100	~			
Peak repetitive forward current per leg		I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 150 $^{\circ}$ C	16				
Operating junction and storage temperatures		T_J,T_Stg		-65 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS MIN. TYP. MAX.						
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-			
Forward valtage	V _F	I _F = 8 A	-	-	0.975	V		
Forward voltage	۷F	I _F = 8 A, T _J = 150 °C	-	-	0.895			
		$V_{R} = V_{R}$ rated	-	-	5			
Reverse leakage current I _R		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA		
Junction capacitance	CT	V _R = 200 V	-	25	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

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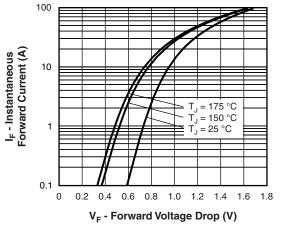
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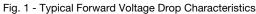
DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µs, V _R = 30 V	-	-	35		
Reverse recovery time	t _{rr}	$I_F = 0.5 \text{ A}, I_R = 1.0$	A, I _{REC} = 0.25 A	-	-	25	ns	
neverse recovery time		T _J = 25 °C		-	20	-		
		T _J = 125 °C	-	34	-			
Dook roooyony ourront	BBM	T _J = 25 °C	I _F = 8 A dI _F /dt = 200 A/μs	-	1.7	-	٨	
Peak recovery current		T = 125 °C	$V_{\rm R} = 160 {\rm V}$	-	4.2	-	A	
Reverse recovery charge	0	T _J = 25 °C		-	23	-	nC	
	Q _{rr}	T _J = 125 °C		-	75	-		

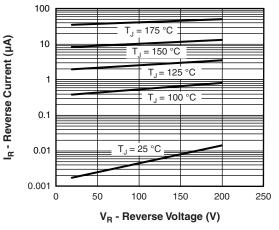
THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to case per leg	R _{thJC}		-	-	3.0		
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	50	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-		
Weight			-	2.0	-	g	
weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AB		MUR1	620CT		

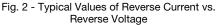


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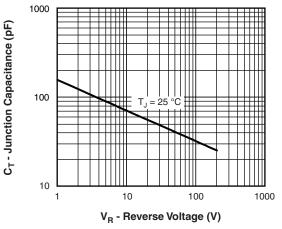


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

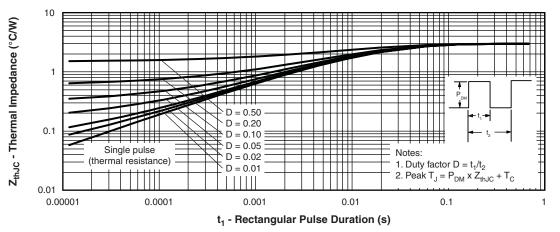
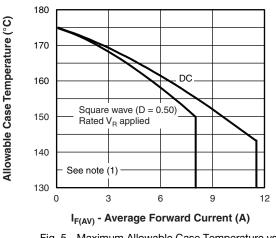


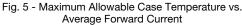
Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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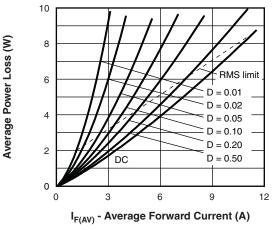
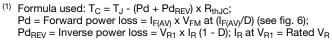


Fig. 6 - Forward Power Loss Characteristics

Note



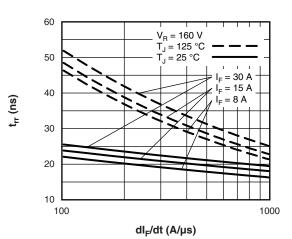
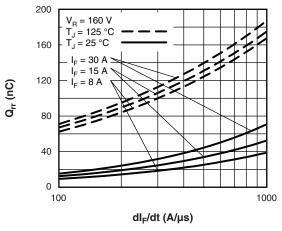


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt





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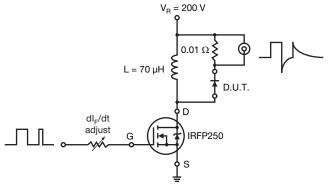


Fig. 9 - Reverse Recovery Parameter Test Circuit

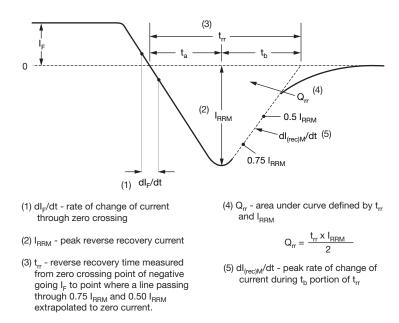


Fig. 10 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code	VS-	MUR	16	20	СТ	PbF	
		2	3	4	5	6	
	1 - 2 - 3 - 4 - 5 - 6 -	Ultra Cur Volt CT	nay Sem afast MU rent ratii age rati = centei ironmer	JR serie ng (16 = ng (20 = r tap (du	es : 16 A) : 200 V) ial)		
				0		oHS-co	mpliar

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-MUR1620CTPbF	50	1000	Antistatic plastic tube				
VS-MUR1620CT-N3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95222						
	TO-220ABPbF	www.vishay.com/doc?95225				
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028				



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches





.ead	assignments

Diodes

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 10.51 0.414 10.11 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 L L1 3.32 3.82 0.131 0.150 2 ØΡ 3.54 3.73 0.139 0.147 2.60 0.102 Q 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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